Integrated Device Technology, Inc.

BiCMOS HIGH-SPEED STATIC RAM 72K (8K x 9-BIT)

ADVANCE INFORMATION
IDT71B69

FEATURES:

- 8192-words x 9-bits organization
- Fast access time:
  - — Commercial: 12/15/20ns
  - — Military: 15/20ns
- Produced with advanced BiCEMOS™ high-performance technology
- JEDEC standard 28-pin DIP/SOJ and 32-pin LCC
- Single 5V power supply
- Inputs and outputs directly TTL compatible

DESCRIPTION:

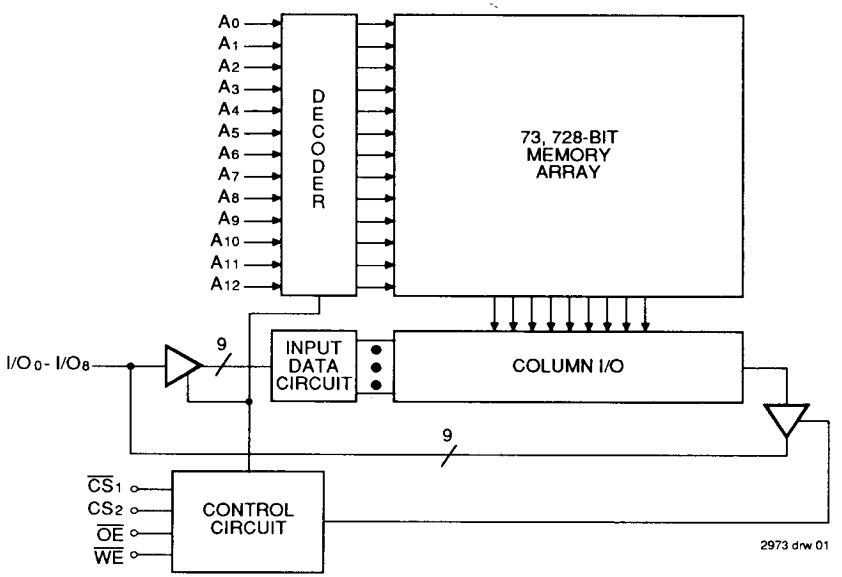
The IDT71B69 is a 73,728-bit high-speed static RAM, organized as 8K x 9. It is fabricated using IDT's high-performance, high-reliability BiCEMOS technology.

The IDT71B69 offers address access times as fast as 12ns. The ninth bit is optimal for systems using parity.

All inputs and outputs of the IDT71B69 are TTL-compatible. The device has 2 chip selects for simplified address decoding.

The IDT71B69 is packaged in an industry standard 300-mil 28-pin DIP/SOJ and 32-pin LCC.

FUNCTIONAL BLOCK DIAGRAM



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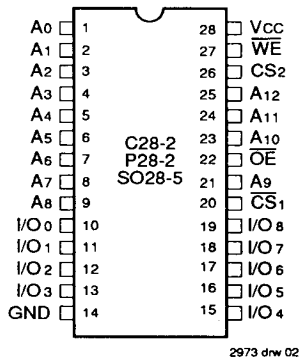
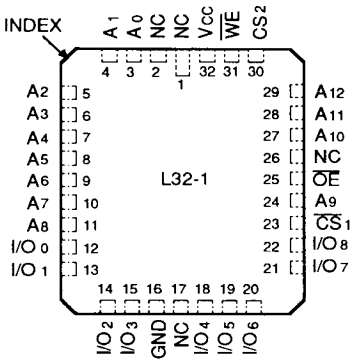
PIN CONFIGURATIONS



DIP/SOJ
TOP VIEW



LCC
TOP VIEW

TRUTH TABLE(1)

CS2	CS1	OE	WE	I/O	Function
X	H	X	X	Hi-Z	Deselect chip
L	X	X	X	Hi-Z	Deselect chip
H	L	L	H	DOUT	Read
H	L	X	L	DIN	Write
H	L	H	H	Hi-Z	Output Disabled

NOTE: 2973 tbl 01
1. H = VIH, L = VIL, X = Don't Care.

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Rating	Com'l.	Mil.	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
TA	Operating Temperature	0 to +70	-55 to +125	°C
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
TSTG	Storage Temperature	-55 to +125	-65 to +135	°C
IOUT	DC Output Current	50	50	mA

NOTE: 2973 tbl 02
1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

Grade	Temperature	GND	VCC
Military	-55°C to +125°C	0V	5V ± 10%
Commercial	0°C to +70°C	0V	5V ± 10%

2973 tbl 02

CAPACITANCE (TA = +25°C, f = 1.0MHz)

Symbol	Parameter(1)	Conditions	Max.	Unit
CIN	Input Capacitance	VIN = 0V	8	pF
COUT	Output Capacitance	VOUT = 0V	8	pF

NOTE: 2973 tbl 03
1. This parameter is determined by device characterization, but is not production tested.

RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min.	Typ.	Max.	Unit
VCC	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
VIH	Input High Voltage	2.2	—	6.0	V
VIL	Input Low Voltage	-0.5(1)	—	0.8	V

NOTE: 2973 tbl 05
1. 1.5V undershoots are allowed for 10ns once per cycle.

DC ELECTRICAL CHARACTERISTICS[1]

(V_{CC} = 5.0V ± 10%)

Symbol	Parameter	71B69S12		71B69S15		71B69S20		Unit
		Com'l.	Mil.	Com'l.	Mil.	Com'l.	Mil.	
I_{CC}	Dynamic Operating Current $\overline{CS_1}$ = V_{IL}, CS_2 = V_{IH}, Outputs Open, V_{CC} = Max., f = f_{MAX}[2]	180	—	180	—	180	190	mA

NOTES:
1. All values are maximum guaranteed values.
2. f_{MAX} = 1/t_{RC}.

2958 tbl 05

DC ELECTRICAL CHARACTERISTICS

V_{CC} = 5.0V ± 10%

Symbol	Parameter	Test Condition	IDT71B69S		Unit
			Min.	Max.	
$\|I_{LI}\|$	Input Leakage Current	V_{CC} = Max., V_{IN} = GND to V_{CC}	—	5	µA
$\|I_{LO}\|$	Output Leakage Current	V_{CC} = Max., $\overline{CS_1}$ = V_{IH}, CS_2 = V_{IL}, V_{OUT} = GND to V_{CC}	—	5	µA
V_{OL}	Output Low Voltage	I_{OL} = 8mA, V_{CC} = Min.	—	0.4	V
		I_{OL} = 10mA, V_{CC} = Min.	—	0.5	
V_{OH}	Output High Voltage	I_{OH} = -4mA, V_{CC} = Min.	2.4	—	V

2973 tbl 06

AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figures 1A, 1B & 1C

2973 tbl 07

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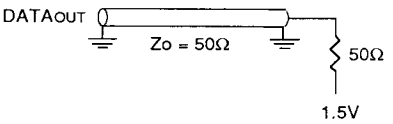
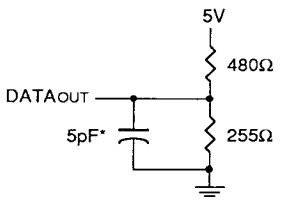


Figure 1A. AC Test Load



*Includes jig and scpe capacitance.

Figure 1B.

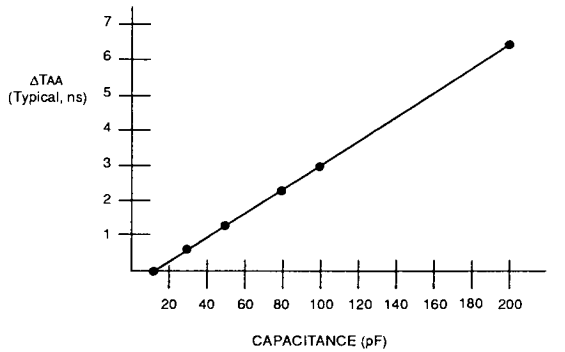


Figure 1C. Lumped Capacitive Load, Typical Derating

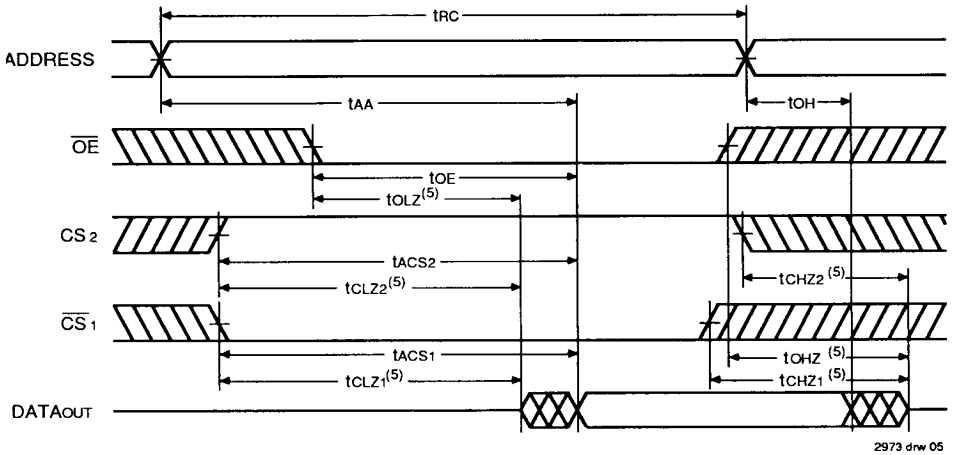
AC ELECTRICAL CHARACTERISTICS (Vcc = 5.0V ± 10%, All Temperature Ranges)

Symbol	Parameter	71B9S12[1] Min.	71B9S12[1] Max.	71B69S15 Min.	71B69S15 Max.	71B69S20 Min.	71B69S20 Max.	Unit
Read Cycle								
tRC	Read Cycle Time	12	—	15	—	20	—	ns
tAA	Address Access Time	—	12	—	15	—	20	ns
tACS1	Chip Select-1 Access Time	—	12	—	15	—	20	ns
tACS2	Chip Select-2 Access Time	—	12	—	15	—	20	ns
tCLZ1,2	Chip Select to Output in Low Z[2]	2	—	3	—	5	—	ns
tOE	Output Enable to Output Valid	—	6	—	7	—	9	ns
tOLZ	Output Enable to Output in Low Z[2]	2	—	3	—	3	—	ns
tCHZ1,2	Chip Select-1, 2 to Output in High Z[2]	—	6	—	7	—	8	ns
tOHZ	Output Disable to Output in High Z[2]	—	5	—	6	—	8	ns
tOH	Output Hold from Address Change	3	—	3	—	5	—	ns
Write Cycle								
tWC	Write Cycle Time	12	—	15	—	20	—	ns
tAW	Address Valid to End of Write	10	—	12	—	15	—	ns
tCW1	Chip Select to End of Write ($\overline{CS_1}$)	10	—	12	—	15	—	ns
tCW2	Chip Select to End of Write (CS_2)	10	—	12	—	15	—	ns
tAS	Address Set-up Time	0	—	0	—	0	—	ns
tWP	Write Pulse Width	9	—	12	—	15	—	ns
tWR1	Write Recovery Time ($\overline{CS_1}$, $\overline{WE}$)	0	—	0	—	0	—	ns
tWR2	Write Recovery Time (CS_2)	—	0	—	3	—	5	ns
tWHZ	Write Enable to Output in High Z[2]	—	6	—	7	—	8	ns
tDW	Data Valid to End of Write	6	—	9	—	10	—	ns
tDH1	Data Hold from Write Time ($\overline{CS_1}$, $\overline{WE}$)	0	—	0	—	0	—	ns
tDH2	Data Hold from Write Time (CS_2)	0	—	0	—	0	—	ns
tOW	Output Active from End of Write[2]	2	—	3	—	5	—	ns

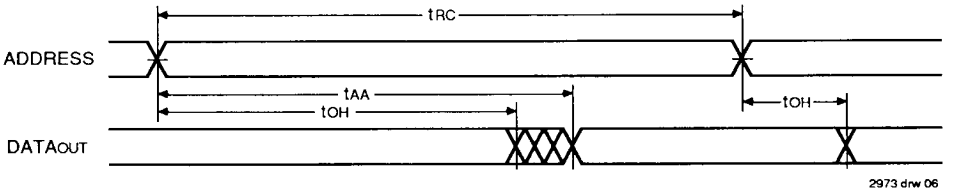
NOTES:
1. 0° to +70°C temperature range only.
2. This parameter is guaranteed with the AC Load, Figure 1B, and is not tested.

2973 tbl 09

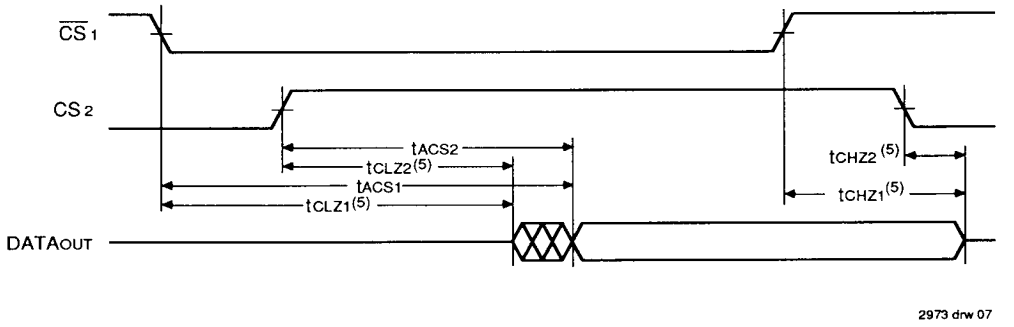
TIMING WAVEFORM OF READ CYCLE NO. 1(1,3)



TIMING WAVEFORM OF READ CYCLE NO. 2(1, 2, 4)

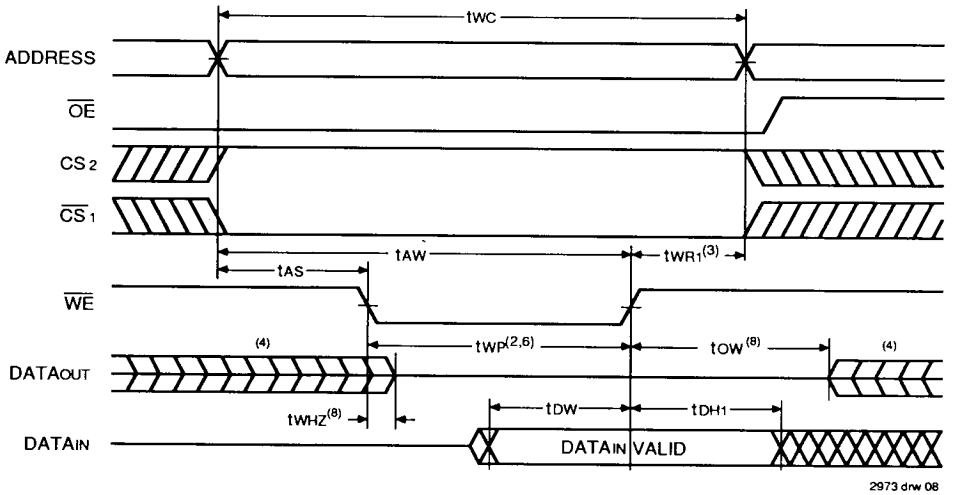


TIMING WAVEFORM OF READ CYCLE NO. 3(1, 3, 4)

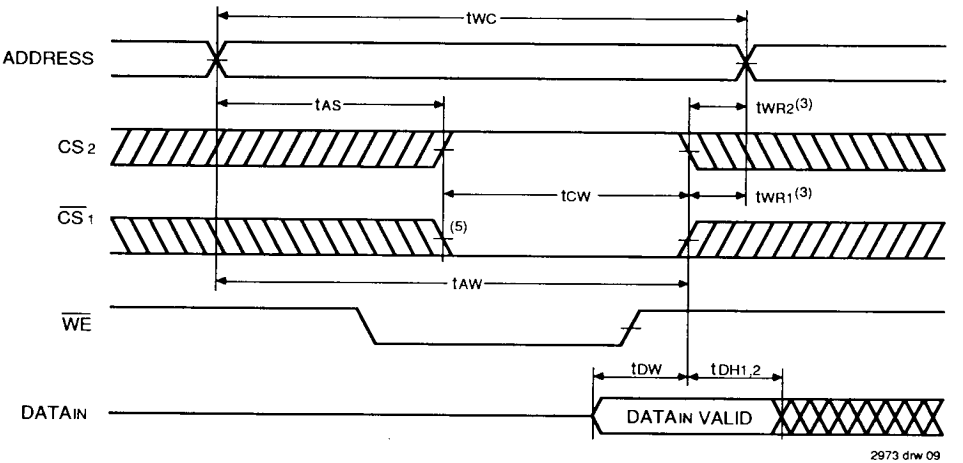


NOTES:
1. $\overline{WE}$ is high for read cycle.
2. Device is continuously selected, $\overline{CS_1}$ = V_{IL}, CS_2 = V_{IH}.
3. Address valid prior to or coincident with $\overline{CS_1}$ transition low and CS_2 transition high.
4. $\overline{OE}$ = V_{IL}.
5. Transition is measured ±200mV from steady state.

TIMING WAVEFORM OF WRITE CYCLE NO. 1 ($\overline{WE}$ CONTROLLED TIMING)(1)

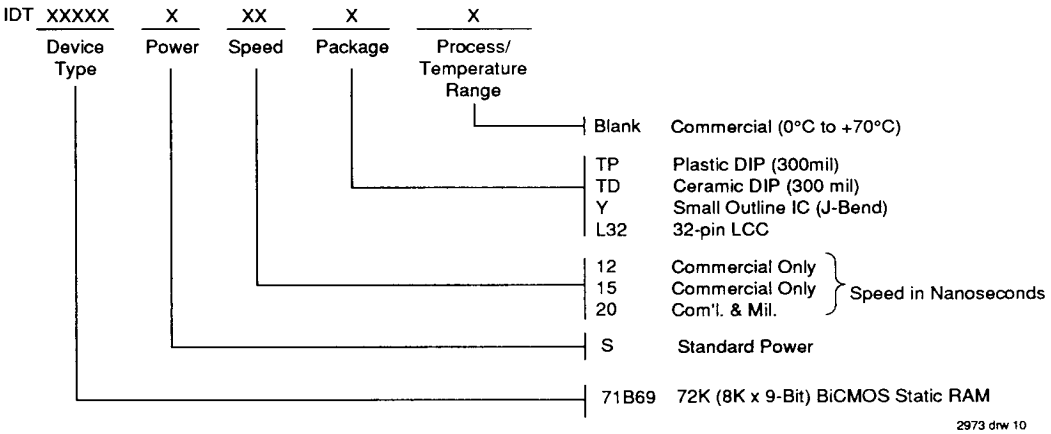


TIMING WAVEFORM OF WRITE CYCLE NO. 2 ($\overline{CS}$ CONTROLLED TIMING)(1)



NOTES:
1. $\overline{WE}$ must be high during all address transitions.
2. A write occurs during the overlap (tWP) of a low $\overline{CS_1}$ and a high CS_2.
3. $t_{WR1,2}$ is measured from the earlier of $\overline{CS_1}$ or $\overline{WE}$ going high or CS_2 going low to the end of the write cycle.
4. During this period, I/O pins are in the output state so that the input signals must not be applied.
5. If the $\overline{CS_1}$ low transition or CS_2 high transiton occurs simultaneously with or after the $\overline{WE}$ low transition, the outputs remain in a high impedance state.
6. If $\overline{OE}$ is low during a $\overline{WE}$ controlled write cycle, the write pulse width must be the larger of tWP or (tWHZ +tDW) to allow the I/O drivers to turn off and data to be placed on the bus for the required tDW. If $\overline{OE}$ is high during a $\overline{WE}$ controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified tWR.
7. DATAOUT is the same phase of write data of this write cycle.
8. Transition is measured ±200mV from steady state.

ORDERING INFORMATION



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